

DESCRIPTION

FEATURES

- The 2SC2412KQ~2SC2412KS are available in SOT-23 package
- Available in SOT-23 package

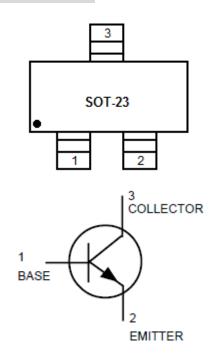
ORDERING INFORMATION

| Package Type | Part Number | | | |
|--|----------------------|--|--|--|
| SOT-23 | 2SC2412KX | | | |
| Note | X = Q, R, S | | | |
| | See below hFE | | | |
| | Classification Table | | | |
| | SPQ: 3,000pcs/Reel | | | |
| AiT provides all RoHS Compliant Products | | | | |

hFE CLASSIFICATION

| Classification | Q | Q R | |
|----------------|---------|---------|---------|
| hFE | 120~270 | 180~390 | 270~560 |

PIN DESCRIPTION





ABSOLUTE MAXIMUM RATINGS

| V _{CEO} , Collector-Emitter Voltage | 50V |
|--|----------------|
| V _{CBO} , Collector-Base Voltage | 60V |
| V _{EBO} , Emitter-Base Voltage | 7.0V |
| Ic, Collector Current-Continuous | 150mAdc |
| P _c , Collector Power Dissipation | 0.2W |
| T _J , Junction Temperature | 150°C |
| T _{STG} , Storage Temperature | -55°C ~ +150°C |

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



ELECTRICAL CHARACTERISTICS

 T_A = 25°C, unless otherwise noted.

| Parameter | Symbol | Characteristic | | Min. | Тур. | Max. | Unit |
|--------------------------------------|----------------------|---|---|------|------|------|------|
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | Ic=1mA | | 50 | I | I | V |
| Emitter-Base Breakdown Voltage | V(BR)EBO | Ι _Ε =50μΑ | | 7 | I | I | V |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | I _C =50μΑ | | 60 | I | I | V |
| Collector Cutoff Current | I _{CBO} | V _{CB} =60V | | - | I | 0.1 | μA |
| Emitter Cutoff Current | I _{EBO} | V _{EB} =7V | | - | - | 0.1 | μA |
| Collector-Emitter Saturation Voltage | V _{CE(sat)} | I _C /I _B =50mA/5mA | | - | - | 0.4 | V |
| DC Current Transfer Ratio | h _{FE} | V _{CE} =6V, I _C =1mA | Q | 120 | - | 270 | |
| | | | R | 180 | - | 390 | - |
| | | | S | 270 | - | 560 | |
| Transition Frequency | f⊤ | V _{CB} =12V, I _E =-2mA, f=30MHz | | - | 180 | - | MHz |
| Output Capacitance | Cob | V_{CB} =12V, I _E =0A, f=1MHz | | - | 2.0 | 3.5 | pF |



TYPICAL CHARACTERISTICS

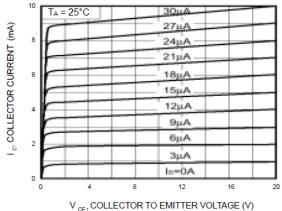
1.

5.

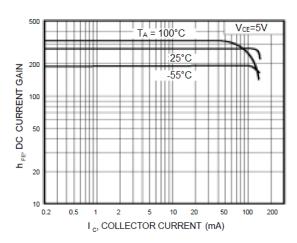
50 V_{CE}= 6 V 20 I $_{\odot}$ COLLECTOR CURRENT (mA) 10 50 55°C 000 25°C 2 0.5 0.2 0.1 0 -0.2 -0.4 -0.6 **--0.8** -1.0 -1.2 -1.4 -1.6 V BE, BASE TO EMITTER VOLTAGE(V)

Grounded emitter propagation characteristics

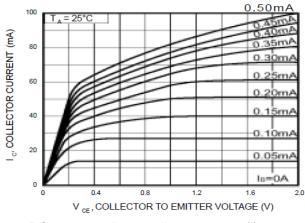
3. Grounded emitter output characteristics(II)



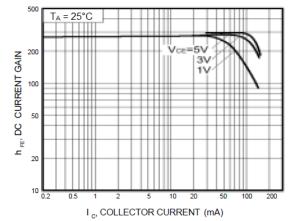
DC current gain vs. collector current (II)



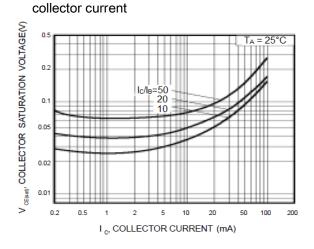
2. Grounded emitter output characteristics(I)



4. DC current gain vs. collector current (I)



6. Collector-emitter saturation voltage vs.

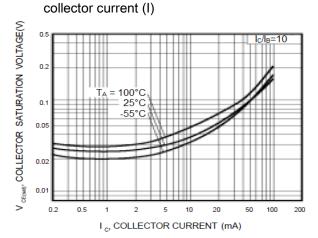




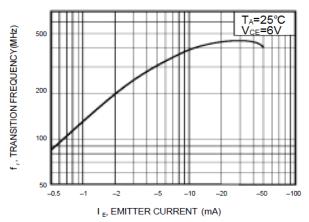
Collector-emitter saturation voltage vs.

7.

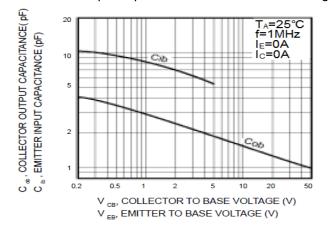
2SC2412KQ~2SC2412KS GENERAL PURPOSE TRANSISTORS PNP SILICON



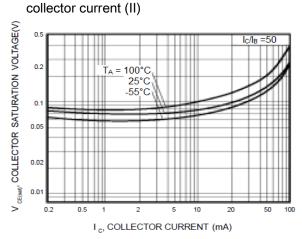
9. Gain bandwidth product vs. emitter current

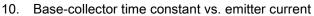


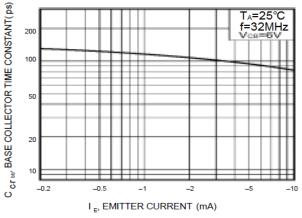
11. Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage



8. Collector-emitter saturation voltage vs.



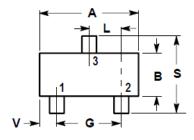


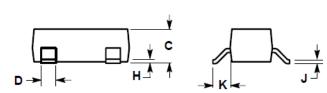


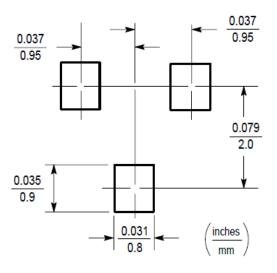


PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)







| DIM | MILLIMETERS | | INCHES | | |
|-----|-------------|-------|--------|--------|--|
| DIM | MIN | MAX | MIN | MAX | |
| А | 2.80 | 3.04 | 0.1102 | 0.1197 | |
| В | 1.20 | 1.40 | 0.0472 | 0.0551 | |
| С | 0.89 | 1.11 | 0.0350 | 0.0440 | |
| D | 0.37 | 0.50 | 0.0150 | 0.0200 | |
| G | 1.78 | 2.04 | 0.0701 | 0.0807 | |
| Н | 0.013 | 0.100 | 0.0005 | 0.0040 | |
| J | 0.085 | 0.177 | 0.0034 | 0.0070 | |
| К | 0.35 | 0.69 | 0.0140 | 0.0285 | |
| L | 0.89 | 1.02 | 0.0350 | 0.0401 | |
| S | 2.10 | 2.64 | 0.0830 | 0.1039 | |
| V | 0.45 | 0.60 | 0.0177 | 0.0236 | |



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